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FDMD8900

N-Channel PowerTrench[®] MOSFET

Q1: 30 V, 66 A, 4 mΩ Q2: 30 V, 42 A, 5.5 mΩ

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 4 mΩ at $V_{GS} = 10 V, I_D = 19 A$
- Max $r_{DS(on)}$ = 5 mΩ at $V_{GS} = 4.5 V, I_D = 17 A$
- Max $r_{DS(on)}$ = 6.5 mΩ at $V_{GS} = 3.8 V, I_D = 15 A$
- Max $r_{DS(on)}$ = 8.3 mΩ at $V_{GS} = 3.5 V, I_D = 14 A$

Q2: N-Channel

- Max $r_{DS(on)}$ = 5.5 mΩ at $V_{GS} = 10 V, I_D = 17 A$
- Max $r_{DS(on)}$ = 6.5 mΩ at $V_{GS} = 4.5 V, I_D = 15 A$
- Max $r_{DS(on)}$ = 9 mΩ at $V_{GS} = 3.8 V, I_D = 13 A$
- Max $r_{DS(on)}$ = 12 mΩ at $V_{GS} = 3.5 V, I_D = 12 A$
- Ideal for Flexible Layout in Primary Side of Bridge Topology
- Termination is Lead-free and RoHS Compliant
- 100% UIL Tested
- Kelvin High Side MOSFET Drive Pin-out Capability

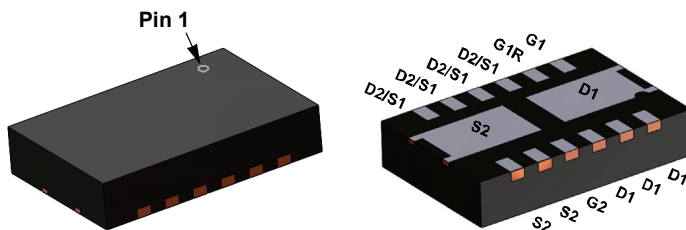


General Description

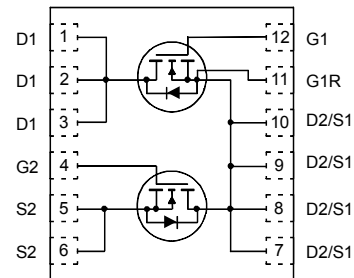
This device utilizes two optimized N-ch FETs in a dual 3.3x5mm thermally enhanced power package. The HS Source and LS drain are internally connected providing a low source inductance package, helping to provide the best FOM.

Applications

- Computing
- Buck, Boost and Buck/Boost Applications
- General Purpose POL



Power 3.3 x 5



MOSFET Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	Q1	Q2	Units
V_{DS}	Drain to Source Voltage	30	30	V
V_{GS}	Gate to Source Voltage	± 12	± 12	V
I_D	Drain Current -Continuous	$T_C = 25^\circ C$ (Note 5)	66	A
	-Continuous	$T_C = 100^\circ C$ (Note 5)	42	
	-Continuous	$T_A = 25^\circ C$ (Note 1a)	19	
	-Pulsed	(Note 4)	280	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	73	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	27	W
	Power Dissipation	$T_A = 25^\circ C$ (Note 1a)	2.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ C$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.7	8.4	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60		

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
8900	FDMD8900	Power 3.3 x 5	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$ $I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$	Q1 Q2	14 13			mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$ $V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$	Q1 Q2			1 1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 12\text{ V}$, $V_{DS} = 0\text{ V}$ $V_{GS} = \pm 12\text{ V}$, $V_{DS} = 0\text{ V}$	Q1 Q2			± 100 ± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$ $V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	Q1 Q2	0.8 1	1.3 1.4	2.5 2.5	mV
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$	Q1 Q2	-4 -4			mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 19\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 17\text{ A}$ $V_{GS} = 3.8\text{ V}$, $I_D = 15\text{ A}$ $V_{GS} = 3.5\text{ V}$, $I_D = 14\text{ A}$ $V_{GS} = 10\text{ V}$, $I_D = 19\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	Q1		3.4 4 4.3 4.6 4.6	4 5 6.5 8.3 6	m Ω
		$V_{GS} = 10\text{ V}$, $I_D = 17\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 15\text{ A}$ $V_{GS} = 3.8\text{ V}$, $I_D = 13\text{ A}$ $V_{GS} = 3.5\text{ V}$, $I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$, $I_D = 17\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	Q2		4.5 5.4 6 6.6 5.8	5.5 6.5 9 12 6.9	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 19\text{ A}$ $V_{DS} = 5\text{ V}$, $I_D = 17\text{ A}$	Q1 Q2		86 80		S

Dynamic Characteristics

C_{iss}	Input Capacitance	Q1: $V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		1735 1210	2605 1815	pF
C_{oss}	Output Capacitance	Q2: $V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		462 356	695 535	pF
C_{riss}	Reverse Transfer Capacitance	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	Q1 Q2		47 52	75 80	pF
R_g	Gate Resistance		Q1 Q2		0.8 1.9		Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time		Q1 Q2		8.7 7.1	17 14	ns
t_r	Rise Time	Q1: $V_{DD} = 15\text{ V}$, $I_D = 19\text{ A}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		2.3 2	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time	Q2: $V_{DD} = 15\text{ V}$, $I_D = 17\text{ A}$, $R_{GEN} = 6\text{ }\Omega$	Q1 Q2		25 22	40 35	ns
t_f	Fall Time		Q1 Q2		2.4 2.3	10 10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 10 V	Q1 Q2		25 19	35 27	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V}$ to 4.5 V	Q1 Q2		12 8.8	17 12	nC
Q_{gs}	Gate to Source Gate Charge	Q2: $V_{DD} = 15\text{ V}$, $I_D = 17\text{ A}$	Q1 Q2		3.6 2.7		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		2.7 2.6		nC

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

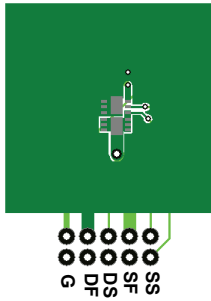
Symbol	Parameter	Test Conditions	Type	Min.	Typ.	Max.	Units
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Drain-Source Diode Characteristics

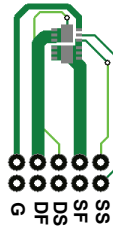
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 19\text{ A}$ (Note 2)	Q1		0.8	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 17\text{ A}$ (Note 2)	Q2		0.8	1.2	
t_{rr}	Reverse Recovery Time	Q1: $I_F = 19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1		26	42	ns
			Q2		22	35	
Q_{rr}	Reverse Recovery Charge	Q2: $I_F = 17\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	Q1		10	20	nC
			Q2		7.8	16	

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $60\text{ }^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b. $130\text{ }^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width $< 300\text{ }\mu\text{s}$, Duty cycle $< 2.0\%$.
- Q1: E_{AS} of 73 mJ is based on starting $T_J = 25\text{ }^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 7\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 25\text{ A}$.
Q2: E_{AS} of 54 mJ is based on starting $T_J = 25\text{ }^\circ\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 20\text{ A}$.
- Pulse I_d refers to Figure "Forward Bias Safe Operation Area".
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

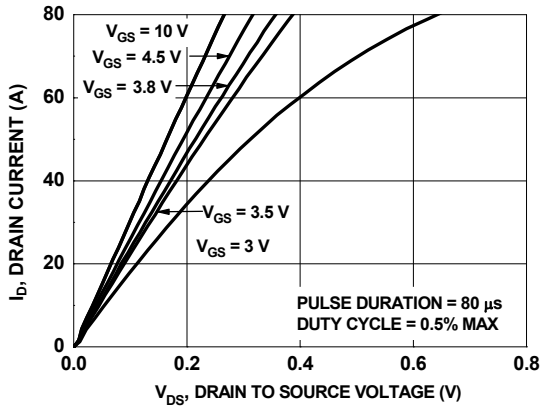


Figure 1. On-Region Characteristics

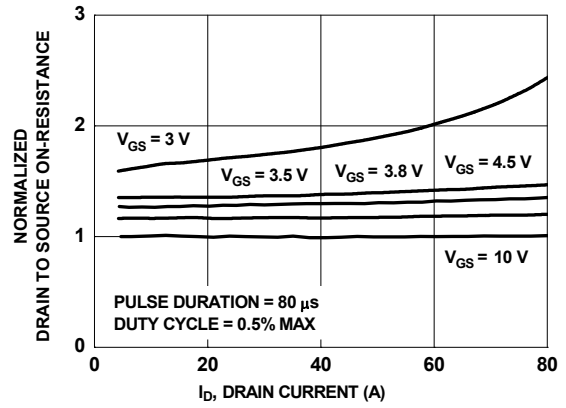


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

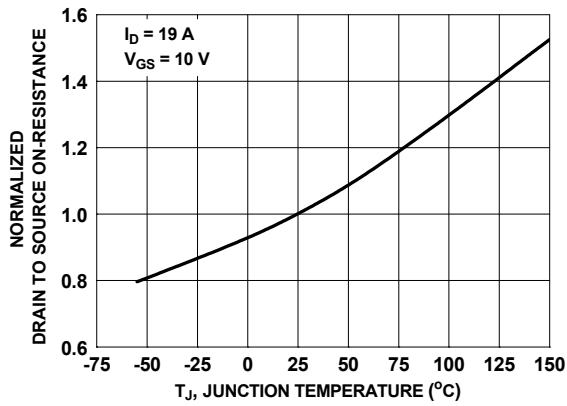


Figure 3. Normalized On Resistance vs. Junction Temperature

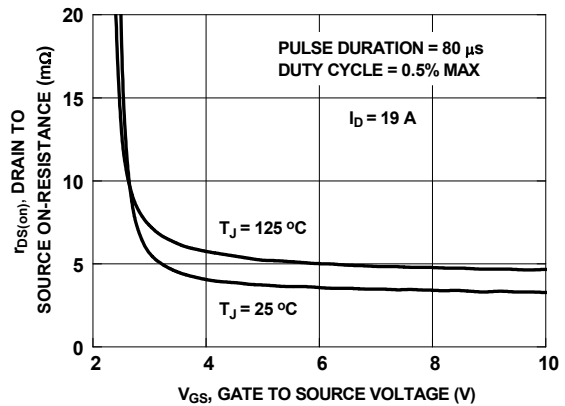


Figure 4. On Resistance vs. Gate to Source Voltage

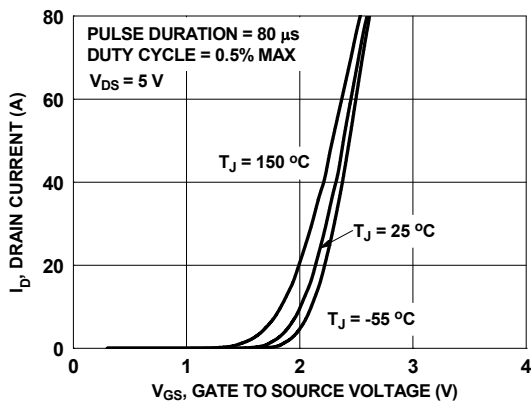


Figure 5. Transfer Characteristics

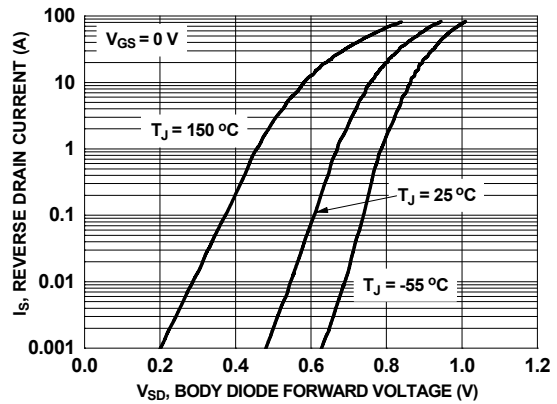


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

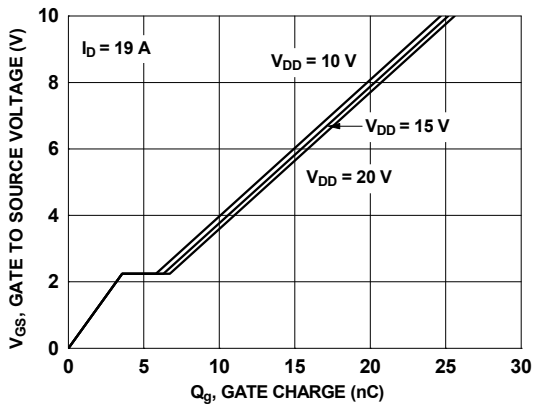


Figure 7. Gate Charge Characteristics

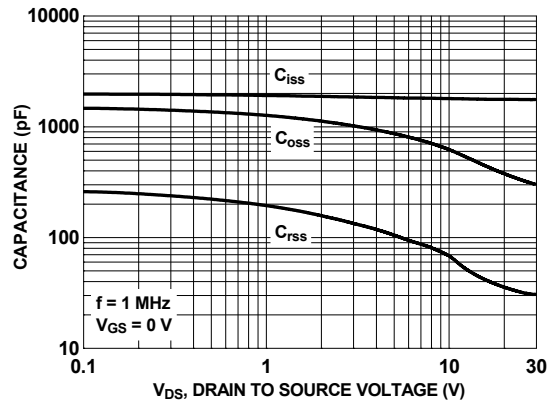


Figure 8. Capacitance vs. Drain to Source Voltage

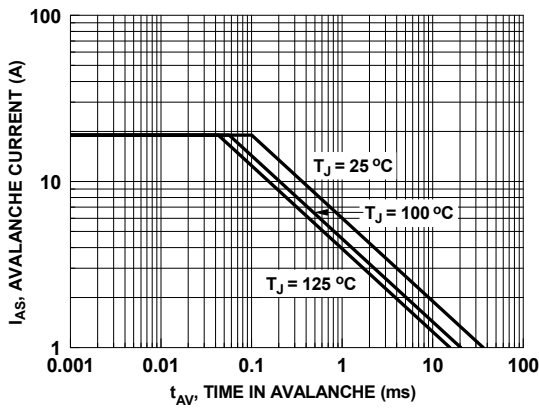


Figure 9. Unclamped Inductive

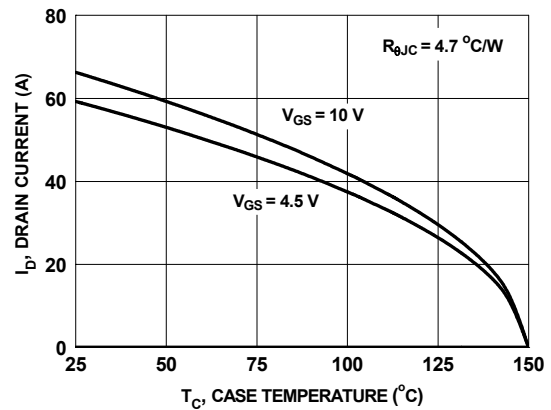


Figure 10. Switching Capability

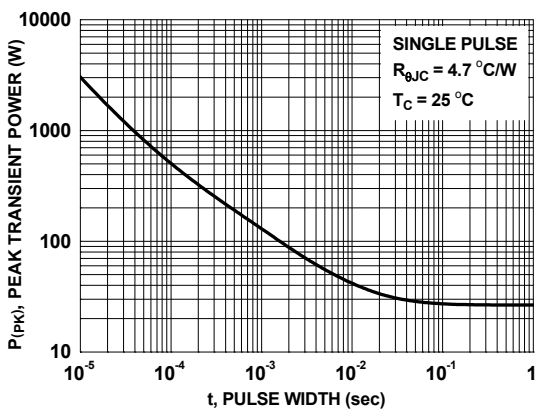


Figure 11. Maximum Continuous Drain Current vs. Case Temperature

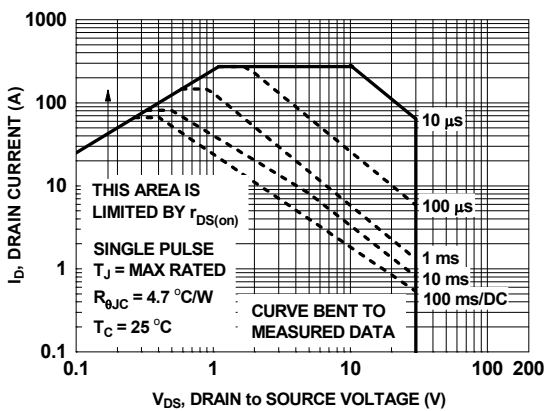


Figure 12. Forward Bias Safe Operating Area

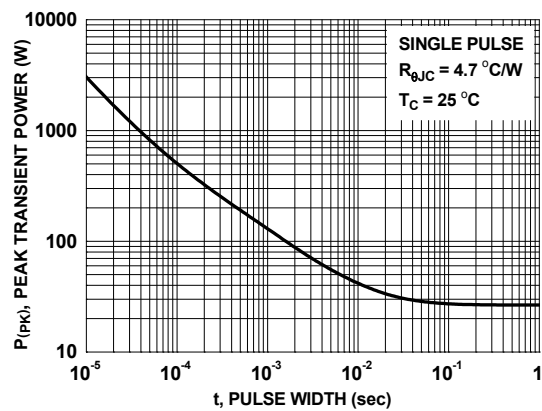


Figure 13. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

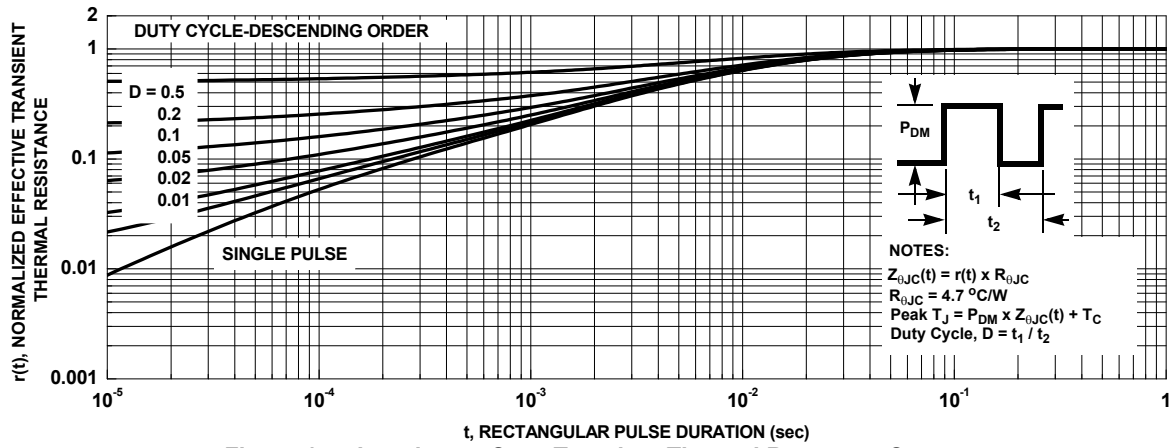


Figure 14. Junction-to-Case Transient Thermal Response Curve

Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

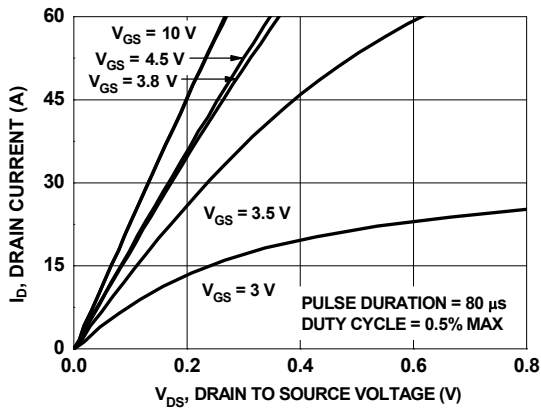


Figure 14. On-Region Characteristics

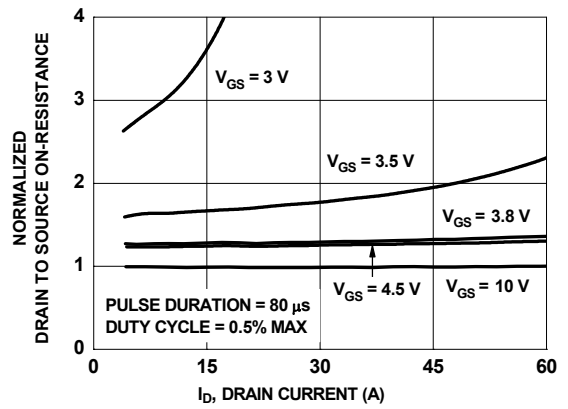


Figure 15. Normalized on-Resistance vs. Drain Current and Gate Voltage

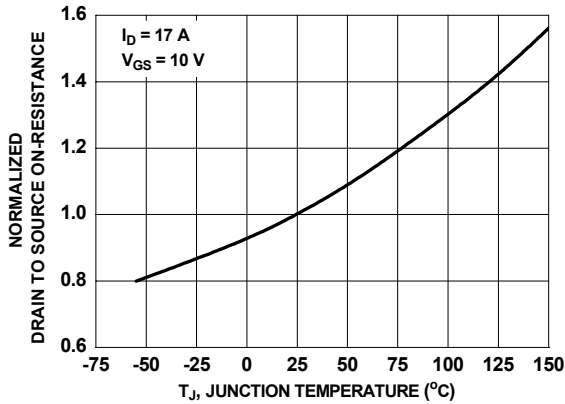


Figure 16. Normalized On-Resistance vs. Junction Temperature

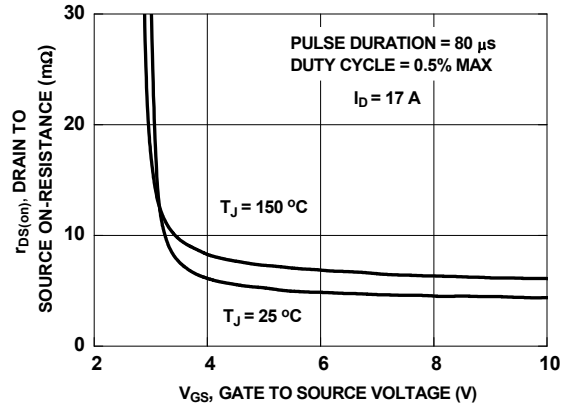


Figure 17. On-Resistance vs. Gate to Source Voltage

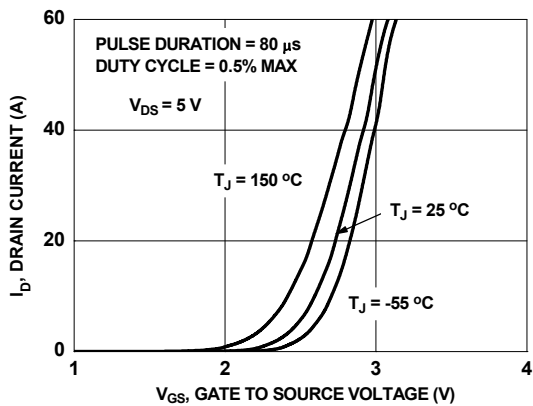


Figure 18. Transfer Characteristics

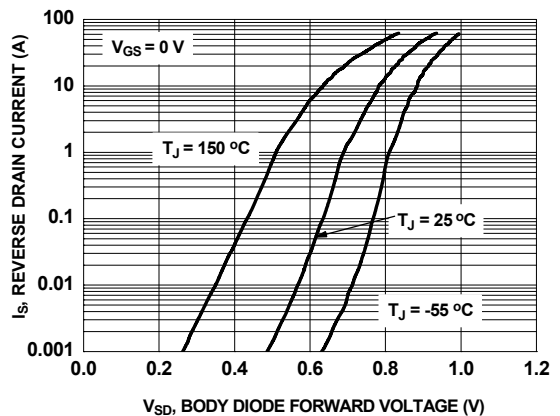


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q2 N-Channel) $T_J = 25^\circ\text{C}$ unless otherwise noted.

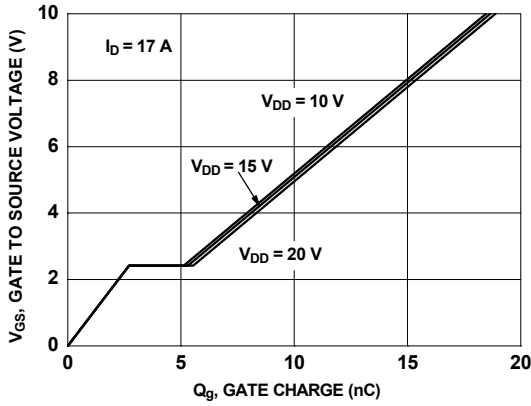


Figure 20. Gate Charge Characteristics

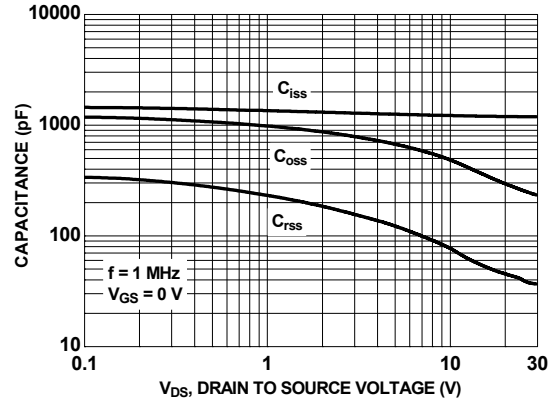


Figure 21. Capacitance vs. Drain to Source Voltage

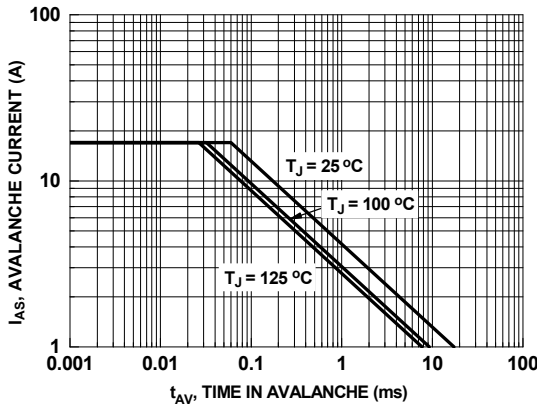


Figure 22. Unclamped Inductive Switching Capability

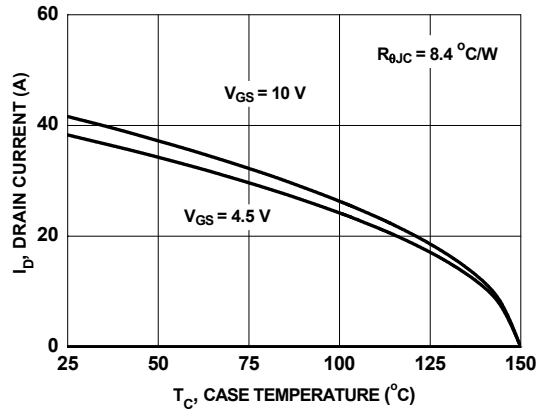


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

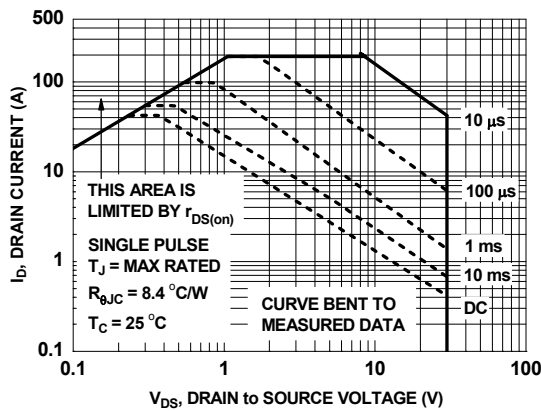


Figure 24. Forward Bias Safe Operating Area

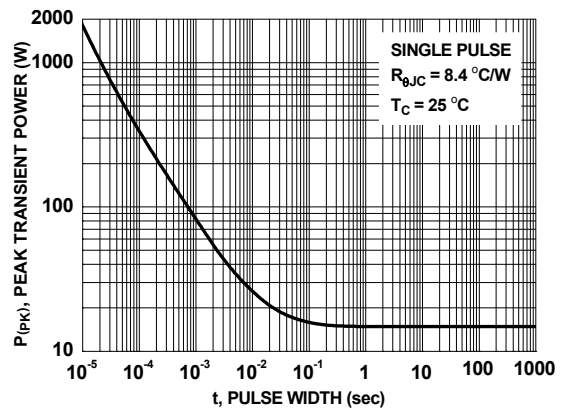


Figure 25. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 N-Channel) $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

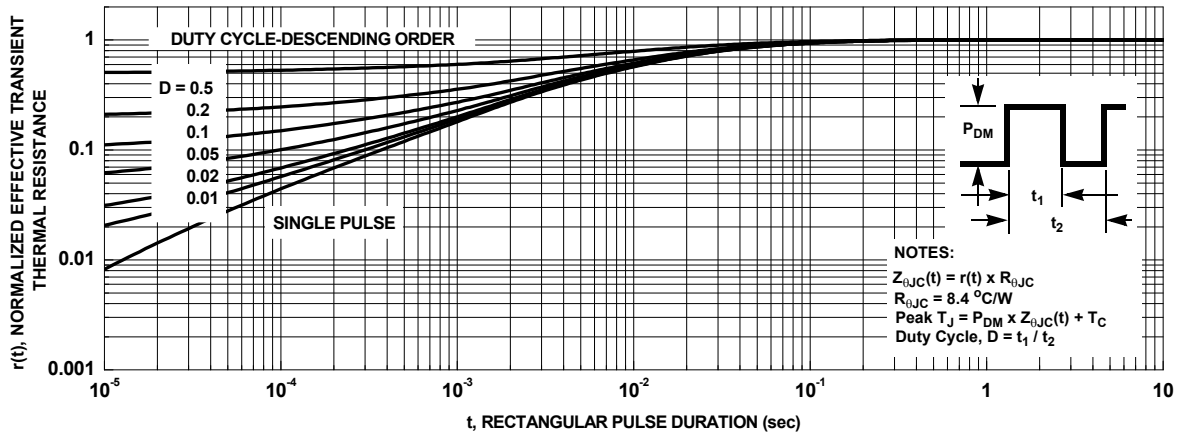
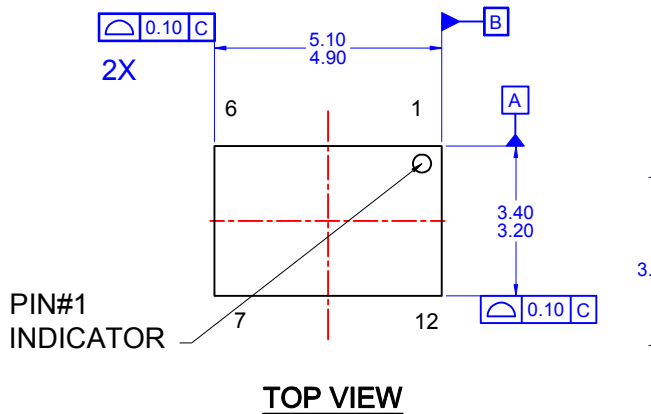


Figure 26. Junction-to-Case Transient Thermal Response Curve

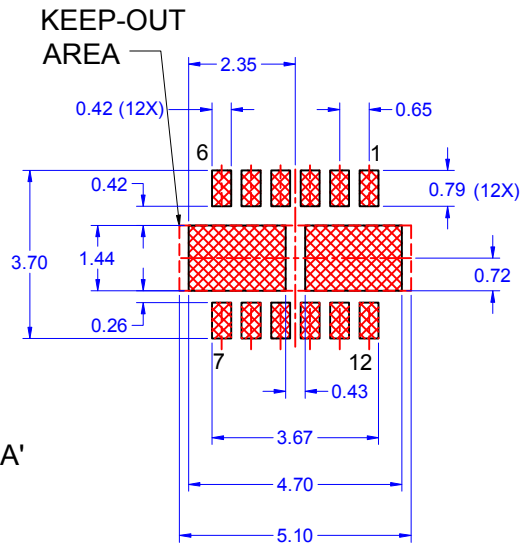


TOP VIEW

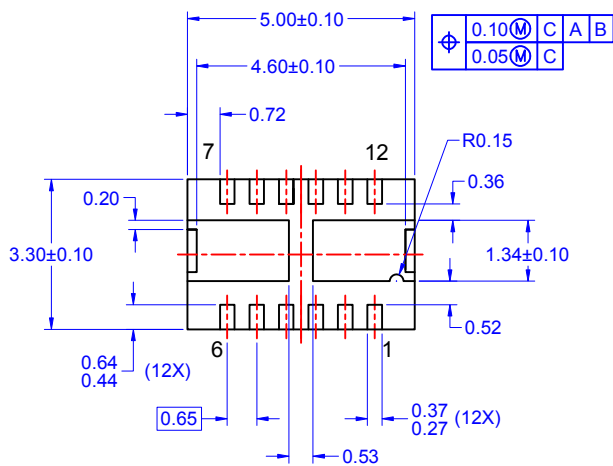


FRONT VIEW

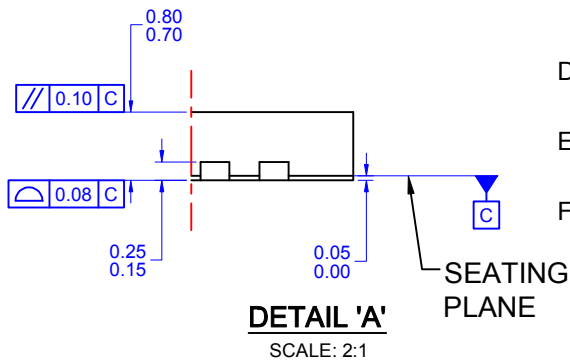
SEE
DETAIL 'A'



**LAND PATTERN
RECOMMENDATION**



BOTTOM VIEW



DETAIL 'A'

SCALE: 2:1

NOTES: UNLESS OTHERWISE SPECIFIED

- A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229 DATED 8/2012
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
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